

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Cancelled).

2. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film comprising silicon over a substrate; and
irradiating said semiconductor film by scanning with at least first and second pairs of linear infrared lights in a predetermined direction,

wherein peaks~~peak~~ of a temperature of the second pair of linear infrared lights are higher than ~~peak~~peaks of a temperature of the first pair of linear infrared lights,

wherein upper lights of the first and second pairs of said linear infrared lights are located over said substrate and lower lights of the first and second pairs of said linear infrared lights are located at a backside of said substrate.

3. (Original) A method according to claim 2, further comprising a step of introducing at least one impurity element into said semiconductor film before said irradiating.

4. (Currently Amended) A method according to claim 2, wherein said semiconductor film comprises a silicon compound represented by Si_xGe_{1-x} .

5. (Currently Amended) A method according to claim 2, further comprising a step of forming a gate electrode over said semiconductor film with a gate insulating film interposed therebetween.

6. (Currently Amended) A method according to claim 2, further comprising a step of forming a gate electrode over said substrate before forming said semiconductor film.

7. (Currently Amended) A method according to claim 2, wherein said semiconductor device havingcomprises an EL display device.

8. (Previously Presented) A method for manufacturing semiconductor device comprising:

forming a semiconductor film over a substrate; and

irradiating said semiconductor film comprising silicon by scanning with at least two main linear infrared lights and two auxiliary linear infrared lights in a predetermined direction so as to form and move a temperature gradient in the semiconductor film,

wherein an upper light of the auxiliary linear infrared lights and an upper light of the main linear infrared lights are located over said semiconductor film and a lower light of the auxiliary linear infrared lights and a lower light of the main linear infrared lights are located at an underside of said semiconductor film.

9. (Original) A method according to claim 8, further comprising a step of introducing at least one impurity element into said semiconductor film before said irradiating.

10. (Currently Amended) A method according to claim 8, wherein said semiconductor film comprises a silicon compound represented by Si_xGe_{1-x} .

11. (Currently Amended) A method according to claim 8, further comprising a step of forming a gate electrode over said semiconductor film with a gate insulating film interposed therebetween.

12. (Currently Amended) A method according to claim 8, further comprising a step of forming a gate electrode over said substrate before forming said semiconductor film.

13. (Currently Amended) A method according to claim 8, wherein said semiconductor device havingcomprises an EL display device.

14. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film comprising silicon over a substrate; and
irradiating said semiconductor film with at least a pair of main linear infrared lights and a pair of auxiliary linear infrared lights while moving said substrate in a direction perpendicular to the linear infrared lights,

wherein an upper light of the auxiliary linear infrared lights and an upper light of the main linear infrared lights is located over said substrate and a lower light of the auxiliary linear infrared lights and a lower light of the main linear infrared lights is located at a backside of said substrate, and

wherein said semiconductor film is irradiated with said auxiliary lights prior to said main linear infrared lights.

15. (Original) A method according to claim 14 further comprising a step of introducing at least one impurity element into said semiconductor film before said irradiating.

16. (Currently Amended) A method according to claim 14 wherein said semiconductor film comprises a silicon compound represented by Si_xGe_{1-x} .

17. (Currently Amended) A method according to claim 14 further comprising a step of forming a gate electrode over said semiconductor film with a gate insulating film interposed therebetween.

18. (Currently Amended) A method according to claim 14 further comprising a step of forming a gate electrode over said substrate before forming said semiconductor film.

19. (Currently Amended) A method according to claim 14 wherein said semiconductor device havingcomprises an EL display device.

20. (Currently Amended) A method for manufacturing semiconductor device comprising:

forming an amorphous semiconductor film comprising silicon over a substrate; and
crystallizing the semiconductor film by scanning with at least first and second upper linear infrared lights and first and second lower linear infrared lights in a predetermined direction,

wherein peakspeak of a temperature of the second upper and lower linear infrared lights are higher than peakpeaks of a temperature of the first upper and lower linear infrared lights,

wherein said first and second upper linear infrared lights are located over said substrate and said first and second lower linear infrared lights are located wherein at a backside of said substrate, and

wherein said predetermined direction is coincident with a direction of crystal growth in the semiconductor film.

21. (Currently Amended) A method according to claim 20, wherein a temperature gradient ~~areis~~ is formed in said semiconductor film and moves in the predetermined direction.

22. (Previously Presented) A method according to claim 20, wherein the first upper linear infrared lights and the first lower linear infrared lights are auxiliary lights, respectively.

23. (Original) A method according to claim 22, wherein the direction of the crystal growth is parallel with the semiconductor film.

24. (Currently Amended) A method according to claim 22, wherein a speed of said scanning is correspondingcorresponds to a rate of the crystal growth.

25. (Currently Amended) A method according to claim 20, wherein semiconductor film comprises a silicon compound represented by Si_xGe_{1-x} .

26. (Currently Amended) A method according to claim 20, further comprising a step of forming a gate electrode over said semiconductor film with a gate insulating film interposed therebetween.

27. (Currently Amended) A method according to claim 20, further comprising a step of forming a gate electrode over said substrate before forming said semiconductor film.

28. (Original) A method according to claim 20, wherein said device is an EL display device.

29. (Previously Presented) A method for manufacturing semiconductor device comprising:

forming an amorphous semiconductor film comprising silicon over a substrate; and
crystallizing the semiconductor film by scanning the semiconductor film with at least a pair of first upper and first lower linear infrared lights and a pair of second upper and second lower linear infrared lights in a direction in order to form and move a temperature gradient the semiconductor film,

wherein said upper linear infrared light are located over said semiconductor film and said at least two lower linear infrared light are located at an underside of said semiconductor film, and

wherein said direction is coincident with a direction of crystal growth to be proceeded in the semiconductor film.

30. (Currently Amended) A method according to claim 29, wherein ~~peak~~peaks of a temperature of the first upper and first lower linear infrared lights are lower than ~~peak-peaks~~ of a temperature of second upper and second lower linear infrared lights.

31. (Original) A method according to claim 29, wherein crystal growth in the semiconductor film expends in the direction parallel with the semiconductor film.

32. (Currently Amended) A method according to claim 29, wherein the semiconductor film comprises a silicon compound represented by Si_xGe_{1-x} .

33. (Currently Amended) A method according to claim 29, further comprising a step of forming a gate electrode over said semiconductor film with a gate insulating film interposed therebetween.

34. (Currently Amended) A method according to claim 29, further comprising a step of forming a gate electrode over said substrate before forming said semiconductor film.

35. (Original) A method according to claim 29, wherein said device is an EL display device.

36. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming an amorphous semiconductor film comprising silicon over a substrate; and
crystallizing said semiconductor film by irradiating said semiconductor film with at least
a pair of main linear infrared lights and a pair of auxiliary linear infrared lights while moving
said substrate in a direction perpendicular to the linear infrared lights,

wherein peakpeak of a temperature of the pair of main linear infrared lights are
higher than peakpeak of a temperature of the pair of auxiliary linear infrared lights,

wherein one of said main linear infrared lights and one of the auxiliary linear
infrared lights are located over said substrate and the other one of said main linear infrared lights
and the other one of the auxiliary linear infrared lights are located at a backside of said substrate,

wherein an irradiating direction is coincident with a direction of crystal growth to
be proceeded in the semiconductor film, and

wherein said semiconductor film is irradiated with said auxiliary lights prior to
said main linear infrared lights.

37. (Currently Amended) A method according to claim 36, wherein said semiconductor
film comprises a silicon compound represented by Si_xGe_{1-x} .

38. (Currently Amended) A method according to claim 36, further comprising a step of
forming a gate electrode over said semiconductor film with a gate insulating film interposed
therebetween.

39. (Currently Amended) A method according to claim 36, further comprising a step of
forming a gate electrode over said substrate before forming said semiconductor film.

40. (Currently Amended) A method according to claim 36, wherein said semiconductor
device havingcomprises an EL display device.

41. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming an amorphous semiconductor film comprising silicon over a substrate; and
crystallizing said semiconductor film by scanning with first and second pairs of linear infrared lights in a direction perpendicular to a longitudinal direction of the linear infrared lights, each of said first and second pairs of linear infrared lights consisting of an upper light and a lower light,

wherein upper lights of the first and second pairs of linear infrared lights are located over said substrate and lower lights of the first and second pairs of linear infrared lights are located at a backside of said substrate, and

wherein said semiconductor film is irradiated with the first upper and lower lights prior to second upper and lower linear infrared lights.

42. (Currently Amended) A method according to claim 41, wherein said semiconductor film comprises a silicon compound represented by Si_xGe_{1-x} .

43. (Currently Amended) A method according to claim 41, further comprising a step of forming a gate electrode over said semiconductor film with a gate insulating film interposed therebetween.

44. (Currently Amended) A method according to claim 41, further comprising a step of forming a gate electrode over said substrate before forming said semiconductor film.

45. (Currently Amended) A method according to claim 41, wherein said semiconductor device havingcomprises an EL display device.

46-48. (Cancelled)